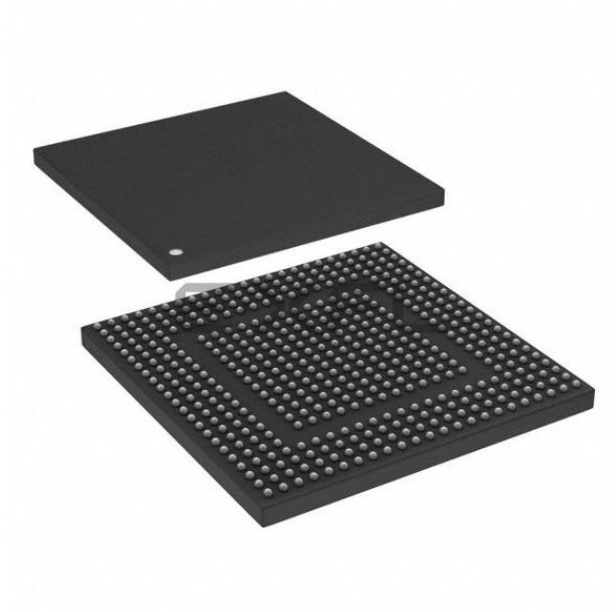

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z7d
Core Size	32-Bit Dual-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, FlexRay, I²C, LINbus, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	-
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.14V ~ 5.5V
Data Converters	A/D 34x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	473-LFBGA
Supplier Device Package	473-MAPBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5675kff0mms2

1.5 Feature list

- High-performance e200z7d dual core
  - 32-bit Power Architecture® technology CPU
  - Up to 180 MHz core frequency
  - Dual-issue core
  - Variable length encoding (VLE)
  - Memory management unit (MMU) with 64 entries
  - 16 KB instruction cache and 16 KB data cache
- Memory available
  - Up to 2 MB code flash memory with ECC
  - 64 KB data flash memory with ECC
  - Up to 512 KB on-chip SRAM with ECC
- SIL3/ASILD innovative safety concept: LockStep mode and fail-safe protection
  - Sphere of replication (SoR) for key components
  - Redundancy checking units on outputs of the SoR connected to FCCU
  - Fault collection and control unit (FCCU)
  - Boot-time built-in self-test for memory (MBIST) and logic (LBIST) triggered by hardware
  - Boot-time built-in self-test for ADC and flash memory
  - Replicated safety-enhanced watchdog timer
  - Silicon substrate (die) temperature sensor
  - Non-maskable interrupt (NMI)
  - 16-region memory protection unit (MPU)
  - Clock monitoring units (CMU)
  - Power management unit (PMU)
  - Cyclic redundancy check (CRC) units
- Decoupled Parallel mode for high-performance use of replicated cores
- Nexus Class 3+ interface
- Interrupts
  - Replicated 16-priority interrupt controller
- GPIOs individually programmable as input, output, or special function
- 3 general-purpose eTimer units (6 channels each)
- 3 FlexPWM units with four 16-bit channels per module
- Communications interfaces
  - 4 LINFlex modules
  - 3 DSPI modules with automatic chip select generation
  - 4 FlexCAN interfaces (2.0B Active) with 32 message objects
  - FlexRay module (V2.1) with dual channel, up to 128 message objects and up to 10 Mbit/s
  - Fast Ethernet Controller (FEC)
  - 3 I^2C modules
- Four 12-bit analog-to-digital converters (ADCs)
  - 22 input channels
  - Programmable cross triggering unit (CTU) to synchronize ADC conversion with timer and PWM
- External bus interface
- 16-bit external DDR memory controller
- Parallel digital interface (PDI)

- Reception queue possible by setting more than one Rx message buffer with the same ID
- Backwards compatible with previous FlexCAN modules
- Safety CAN features on 1 CAN module as implemented on MPC5604P

1.6.17 Dual-channel FlexRay controller

- Full implementation of FlexRay Protocol Specification 2.1
- Sixty-four configurable message buffers can be handled
- Message buffers configurable as Tx, Rx, or RxFIFO
- Message buffer size configurable
- Message filtering for all message buffers based on FrameID, cycle count, and message ID
- Programmable acceptance filters for RxFIFO message buffers
- Dual channel, each at up to 10 Mbit/s data rate

1.6.18 Periodic Interrupt Timer (PIT)

The PIT module implements the features below:

- Four general-purpose interrupt timers
- 32-bit counter resolution
- Clocked by system clock frequency
- 32-bit counter for real time interrupt, clocked from main external oscillator
- Can be used for software tick or DMA trigger operation

1.6.19 System Timer Module (STM)

The STM implements the features below:

- Replicated periphery to provide safety measures respective to high safety integrity levels (for example, SIL 3, ASIL D)
- Up-counter with four output compare registers
- OS task protection and hardware tick implementation as per current state-of-the-art AUTOSAR requirement

1.6.20 Motor control (MOTC) peripherals

The peripherals in this section can be used for general-purpose applications, but are specifically designed for motor control (MOTC) applications.

1.6.20.1 FlexPWM

The pulse width modulator module (FlexPWM) contains three PWM channels, each of which is configured to control a single half-bridge power stage. There may also be one or more fault channels.

This PWM is capable of controlling most motor types: AC induction motors (ACIM), permanent magnet AC motors (PMAC), both brushless (BLDC) and brush DC motors (BDC), switched (SRM) and variable reluctance motors (VRM), and stepper motors.

A FlexPWM module implements the following features:

- 16 bits of resolution for center, edge aligned, and asymmetrical PWMs
- Maximum operating frequency lower than or equal to platform frequency
- Clock source not modulated and independent from system clock (generated via auxiliary PLL)
- Fine granularity control for enhanced resolution of the PWM period

VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VDD_ LV_COR		dramc DQS[1]	dramc DM[1]	dramc D[13]	dramc D[12]	N
VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VDD_ LV_COR		dramc D[14]	dramc D[15]	VSS_HV_ DRAM	VDD_HV_ DRAM	P
VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VDD_ LV_COR		VDD_HV_ DRAM_VREF	dramc ADD[3]	dramc CKE	dramc CLKB	R
VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VDD_ LV_COR		dramc ADD[8]	dramc ADD[9]	dramc ADD[1]	dramc CLK	T
VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VSS_ LV_COR	VDD_ LV_COR		dramc ADD[6]	dramc ADD[12]	VDD_HV_ DRAM	dramc ADD[0]	U
VDD_ LV_COR	VDD_ LV_COR	VDD_ LV_COR	VDD_ LV_COR	VDD_ LV_COR	VDD_ LV_COR		lin0 TXD	dramc ADD[13]	VSS_HV_ DRAM	dramc ADD[2]	V
							lin0 RXD	dramc ADD[14]	dramc ADD[7]	dramc ADD[4]	W
VDD_ HV_IO	adc0_adc1 AN[11]	etimer1 ETC[5]	etimer1 ETC[4]	adc1 AN[8]	adc1 AN[6]	TCK	VDD_HV_IO	dramc ADD[15]	dramc ADD[11]	dramc ADD[5]	Y
adc0 AN[8]	adc0_adc1 AN[12]	adc1 AN[0]	adc1 AN[2]	adc1 AN[5]	adc1 AN[7]	TDI	etimer1 ETC[0]	VSS_HV_IO	lin1 TXD	dramc ADD[10]	AA
adc0 AN[7]	adc0_adc1 AN[13]	adc1 AN[1]	adc1 AN[3]	adc1 AN[4]	TDO	TMS	RESERVED	lin1 RXD	VDD_ HV_IO	VSS_ HV_IO	AB
VSS_ HV_ADR_0	adc0_adc1 AN[14]	VDD_ HV_ADR_1	VSS_ HV_ADR_1	VDD_ HV_PMU	VREG_CTRL	VSS_ HV_PMU	$\overline{\text{RESET}}$_ $\overline{\text{SUP}}$	VREG_INT_ ENABLE	VSS_ HV_IO	VSS_ HV_IO	AC
13	14	15	16	17	18	19	20	21	22	23	

Figure 6. MPC5675K 473 MAPBGA pinout (southeast, viewed from above)

2.2 Pin descriptions

The following sections provide signal descriptions and related information about the functionality and configuration for this device.

2.2.1 Pad types

Table 2 lists the pad types used on the MPC5675K.

Table 2. Pad types

Pad Type	Description
GP Slow	Slow buffer with CMOS Schmitt trigger and pullup/pulldown.
GP Slow/Fast	Programmable slow/fast buffer with CMOS Schmitt trigger, pullup/pulldown.
GP Slow/Medium	Programmable slow/medium buffer with CMOS Schmitt trigger, pullup/pulldown. Programmable slow/medium buffer with CMOS Schmitt trigger, pullup/pulldown and Injection proof analog switch.
GP Slow/Symmetric	Programmable slow/symmetric buffer with CMOS Schmitt trigger, pullup/pulldown.
PDI Medium	Medium slew-rate output with four selectable slew rates. Contains an input buffer and weak pullup/pulldown.
PDI Fast	Fast slew-rate output with four selectable slew rates. Contains an input buffer and weak pullup/pulldown.

Table 2. Pad types (continued)

Pad Type	Description
DRAM ACC	Bidirectional DDR pad. Can be configured to support LPDDR half strength, LPDDR full strength, DDR1, DDR2 half strength, DDR2 full strength, and SDR.
DRAM CLK	Differential clock driver.
DRAM DQ	Bidirectional DDR pad with integrated ODT. Can be configured to support LPDDR half strength, LPDDR full strength, DDR1, DDR2 half strength, DDR2 full strength, and SDR.
DRAM ODT CTL	Enable On Die Termination control.
Analog	CMOS Schmitt trigger cell with injection proof analog switch.
Analog Shared	CMOS Schmitt trigger cell with two injection-proof analog switches.

2.2.2 Power supply and reference voltage pins

Table 3 shows the supply pins for the MPC5675K in the 257 MAPBGA package. Table 5 shows the supply pins for the MPC5675K in the 473 MAPBGA package.

Table 4 and Table 6 show the pins not populated on the MPC5675K 257 MAPBGA and 473 MAPBGA packages, respectively.

Table 3. 257 MAPBGA supply pins

Ball number	Ball name	Pad type	Ball number	Ball name	Pad type
V_{DD}					
A3	VDD_HV_IO	VDD_HV	F9	VDD_LV_COR	VDD_LV
A9	VDD_HV_IO	VDD_HV	F10	VDD_LV_COR	VDD_LV
B16	VDD_HV_IO	VDD_HV	F11	VDD_LV_COR	VDD_LV
C1	VDD_HV_IO	VDD_HV	F12	VDD_LV_COR	VDD_LV
G2	VDD_HV_IO	VDD_HV	G6	VDD_LV_COR	VDD_LV
M2	VDD_HV_IO	VDD_HV	G12	VDD_LV_COR	VDD_LV
P10	VDD_HV_IO	VDD_HV	H6	VDD_LV_COR	VDD_LV
P14	VDD_HV_IO	VDD_HV	H12	VDD_LV_COR	VDD_LV
T2	VDD_HV_IO	VDD_HV	J6	VDD_LV_COR	VDD_LV
T16	VDD_HV_IO	VDD_HV	J12	VDD_LV_COR	VDD_LV
L14	VDD_HV_DRAM_VREF	VDD_HV	K6	VDD_LV_COR	VDD_LV
D8	VDD_HV_FLA	VDD_HV	K12	VDD_LV_COR	VDD_LV
M1	VDD_HV_OSC	VDD_HV	L6	VDD_LV_COR	VDD_LV
D14	VDD_HV_PDI	VDD_HV	L12	VDD_LV_COR	VDD_LV
H16	VDD_HV_PDI	VDD_HV	M6	VDD_LV_COR	VDD_LV
U14	VDD_HV_PMU	VDD_HV	M7	VDD_LV_COR	VDD_LV
R7	VDD_HV_ADR_13	VDD_HV_A	M8	VDD_LV_COR	VDD_LV

Table 5. 473 MAPBGA supply pins (continued)

Ball number	Ball name	Pad type	Ball number	Ball name	Pad type
D13	VDD_HV_FLA	VDD_HV	V6	VDD_LV_COR	VDD_LV
V1	VDD_HV_OSC	VDD_HV	V7	VDD_LV_COR	VDD_LV
D16	VDD_HV_PDI	VDD_HV	V8	VDD_LV_COR	VDD_LV
D20	VDD_HV_PDI	VDD_HV	V9	VDD_LV_COR	VDD_LV
AC17	VDD_HV_PMU	VDD_HV	V10	VDD_LV_COR	VDD_LV
F6	VDD_LV_COR	VDD_LV	V11	VDD_LV_COR	VDD_LV
F7	VDD_LV_COR	VDD_LV	V12	VDD_LV_COR	VDD_LV
F8	VDD_LV_COR	VDD_LV	V13	VDD_LV_COR	VDD_LV
F9	VDD_LV_COR	VDD_LV	V14	VDD_LV_COR	VDD_LV
F10	VDD_LV_COR	VDD_LV	V15	VDD_LV_COR	VDD_LV
F11	VDD_LV_COR	VDD_LV	V16	VDD_LV_COR	VDD_LV
F12	VDD_LV_COR	VDD_LV	V17	VDD_LV_COR	VDD_LV
F13	VDD_LV_COR	VDD_LV	V18	VDD_LV_COR	VDD_LV
F14	VDD_LV_COR	VDD_LV	Y4	VDD_LV_PLL	VDD_LV
V_{SS}					
A2	VSS_HV_IO	VSS_HV	L7	VSS_LV_COR	VSS_LV
A22	VSS_HV_IO	VSS_HV	L8	VSS_LV_COR	VSS_LV
A23	VSS_HV_IO	VSS_HV	L9	VSS_LV_COR	VSS_LV
B1	VSS_HV_IO	VSS_HV	L10	VSS_LV_COR	VSS_LV
B2	VSS_HV_IO	VSS_HV	L11	VSS_LV_COR	VSS_LV
B14	VSS_HV_IO	VSS_HV	L12	VSS_LV_COR	VSS_LV
B23	VSS_HV_IO	VSS_HV	L13	VSS_LV_COR	VSS_LV
C3	VSS_HV_IO	VSS_HV	L14	VSS_LV_COR	VSS_LV
D9	VSS_HV_IO	VSS_HV	L15	VSS_LV_COR	VSS_LV
D11	VSS_HV_IO	VSS_HV	L16	VSS_LV_COR	VSS_LV
H2	VSS_HV_IO	VSS_HV	L17	VSS_LV_COR	VSS_LV
K20	VSS_HV_IO	VSS_HV	M7	VSS_LV_COR	VSS_LV
L4	VSS_HV_IO	VSS_HV	M8	VSS_LV_COR	VSS_LV
N2	VSS_HV_IO	VSS_HV	M9	VSS_LV_COR	VSS_LV
A1	VSS_HV_IO	VSS_HV	M10	VSS_LV_COR	VSS_LV
R4	VSS_HV_IO	VSS_HV	M11	VSS_LV_COR	VSS_LV
W2	VSS_HV_IO	VSS_HV	M12	VSS_LV_COR	VSS_LV
Y12	VSS_HV_IO	VSS_HV	M13	VSS_LV_COR	VSS_LV
AA3	VSS_HV_IO	VSS_HV	M14	VSS_LV_COR	VSS_LV

2.2.4 Multiplexed pins

Table 9 shows the pin multiplexing for the MPC5675K in the 257 MAPBGA package. Table 10 shows the pin multiplexing for the MPC5675K in the 473 MAPBGA package.

Table 9. 257 MAPBGA pin multiplexing

Ball number	Ball type	Ball name	Alternate I/O	Additional inputs	Analog inputs	Weak pull during reset	Pad type	Power domain
A4	GPIO	nexus MDO[5][1]	A0: siul_GPIO[114] A1: _ A2: npc_wrapper_MDO[5] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
A5	GPIO	nexus MDO[7][1]	A0: siul_GPIO[112] A1: _ A2: npc_wrapper_MDO[7] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
A6	GPIO	nexus MDO[9][1]	A0: siul_GPIO[110] A1: _ A2: npc_wrapper_MDO[9] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
A7	GPIO	flexray CB_TX	A0: siul_GPIO[51] A1: flexray_CB_TX A2: _ A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Symmetric	VDD_HV_IO
A8	GPIO	flexray CA_TR_EN	A0: siul_GPIO[47] A1: flexray_CA_TR_EN A2: _ A3: _	I: ctu0_EXT_IN I: flexpwm0_EXT_SYNC I: _	—	disabled	GP Slow/ Symmetric	VDD_HV_IO
A10	GPIO	fec RXD[2]	A0: siul_GPIO[213] A1: _ A2: _ A3: dspi2_SOUT	I: fec_RXD[2] I: _ I: siul_EIRQ[21]	—	disabled	GP Slow/ Medium	VDD_HV_IO
A11	GPIO	fec RX_CLK	A0: siul_GPIO[209] A1: flexray_DBG2 A2: etimer2_ETC[2] A3: dspi0_CS6	I: fec_RX_CLK I: _ I: siul_EIRQ[25]	—	disabled	GP Slow/ Medium	VDD_HV_IO
A12	GPIO	fec RXD[0]	A0: siul_GPIO[211] A1: i2c1_clock A2: _ A3: _	I: fec_RXD[0] I: _ I: siul_EIRQ[27]	—	disabled	GP Slow/ Medium	VDD_HV_IO

Table 9. 257 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional inputs	Analog inputs	Weak pull during reset	Pad type	Power domain
D13	GPIO	fec MDC	A0: siul_GPIO[199] A1: fec_MDC A2: _ A3: _	I: _ I: lin1_RXD I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
D16	GPIO	pdi DATA[0]	A0: siul_GPIO[131] A1: _ A2: lin3_TXD A3: _	I: pdi_DATA[0] I: _ I: flexpwm2_FAULT[2]	—	disabled	PDI Medium	VDD_HV_PDI
D17	GPIO	pdi DATA[1]	A0: siul_GPIO[132] A1: flexpwm2_B[3] A2: _ A3: _	I: pdi_DATA[1] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
E2	GPIO	nexus MDO[1][1]	A0: siul_GPIO[86] A1: _ A2: npc_wrapper_MDO[1] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
E3	GPIO	flexray CA_RX	A0: siul_GPIO[49] A1: _ A2: ctu0_EXT_TGR A3: _	I: flexray_CA_RX I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
E14	GPIO	pdi LINE_V	A0: siul_GPIO[129] A1: _ A2: lin2_TXD A3: _	I: pdi_LINE_V I: _ I: flexpwm2_FAULT[0]	—	disabled	PDI Medium	VDD_HV_PDI
E15	GPIO	pdi DATA[2]	A0: siul_GPIO[133] A1: flexpwm2_A[1] A2: _ A3: etimer1_ETC[2]	I: pdi_DATA[2] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
E16	GPIO	pdi DATA[3]	A0: siul_GPIO[134] A1: flexpwm2_X[1] A2: _ A3: _	I: pdi_DATA[3] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
E17	GPIO	pdi DATA[4]	A0: siul_GPIO[135] A1: flexpwm2_A[2] A2: _ A3: etimer1_ETC[4]	I: pdi_DATA[4] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI

Table 9. 257 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional inputs	Analog inputs	Weak pull during reset	Pad type	Power domain
G3	GPIO	dspi0 SCK	A0: siul_GPIO[37] A1: dspi0_SCK A2: _ A3: sscm_DEBUG[5]	I: flexpwm0_FAULT[3] I: _ I: siul_EIRQ[23]	—	disabled	GP Slow/ Medium	VDD_HV_IO
G4	GPIO	dspi1 SCK	A0: siul_GPIO[6] A1: dspi1_SCK A2: _ A3: _	I: _ I: _ I: siul_EIRQ[6]	—	disabled	GP Slow/ Medium	VDD_HV_IO
G14	GPIO	pdi DATA[9]	A0: siul_GPIO[140] A1: flexpwm2_X[2] A2: _ A3: _	I: pdi_DATA[9] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
G15	GPIO	pdi DATA[10]	A0: siul_GPIO[141] A1: flexpwm2_X[3] A2: _ A3: _	I: pdi_DATA[10] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
G16	GPIO	pdi DATA[11]	A0: siul_GPIO[142] A1: flexpwm2_X[0] A2: _ A3: _	I: pdi_DATA[11] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
G17	GPIO	pdi FRAME_V	A0: siul_GPIO[130] A1: _ A2: _ A3: _	I: pdi_FRAME_V I: lin2_RXD I: flexpwm2_FAULT[1]	—	disabled	PDI Medium	VDD_HV_PDI
H1	GPIO	nexus MDO[10][1]	A0: siul_GPIO[109] A1: _ A2: npc_wrapper_MDO[10] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
H3	GPIO	dspi0 CS0	A0: siul_GPIO[36] A1: dspi0_CS0 A2: _ A3: sscm_DEBUG[4]	I: _ I: _ I: siul_EIRQ[22]	—	disabled	GP Slow/ Medium	VDD_HV_IO
H4	GPIO	dspi1 CS0	A0: siul_GPIO[5] A1: dspi1_CS0 A2: _ A3: dspi0_CS7	I: _ I: _ I: siul_EIRQ[5]	—	disabled	GP Slow/ Medium	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
D1	GPIO	nexus MDO[1][1]	A0: siul_GPIO[86] A1: _ A2: npc_wrapper_MDO[1] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
D2	GPIO	nexus MDO[3][1]	A0: siul_GPIO[84] A1: _ A2: npc_wrapper_MDO[3] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
D3	GPIO	can1 RXD	A0: siul_GPIO[15] A1: _ A2: _ A3: _	I: can1_RXD I: can0_RXD I: siul_EIRQ[14]	—	disabled	GP Slow/ Medium	VDD_HV_IO
D4	GPIO	dspi0 SOUT	A0: siul_GPIO[38] A1: dspi0_SOUT A2: _ A3: sscm_DEBUG[6]	I: _ I: _ I: siul_EIRQ[24]	—	disabled	GP Slow/ Medium	VDD_HV_IO
D6	GPIO	etimer0 ETC[5]	A0: siul_GPIO[44] A1: etimer0_ETC[5] A2: _ A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
D7	GPIO	etimer0 ETC[0]	A0: siul_GPIO[0] A1: etimer0_ETC[0] A2: _ A3: _	I: dspi2_SIN I: _ I: siul_EIRQ[0]	—	disabled	GP Slow/ Medium	VDD_HV_IO
D14	GPIO	fec RXD[2]	A0: siul_GPIO[213] A1: _ A2: _ A3: dspi2_SOUT	I: fec_RXD[2] I: _ I: siul_EIRQ[21]	—	disabled	GP Slow/ Medium	VDD_HV_IO
D15	GPIO	fec MDC	A0: siul_GPIO[199] A1: fec_MDC A2: _ A3: _	I: _ I: lin1_RXD I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
D18	GPIO	pdi DATA[11]	A0: siul_GPIO[142] A1: flexpwm2_X[0] A2: _ A3: _	I: pdi_DATA[11] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
E23	GPIO	dramc BA[2]	A0: siul_GPIO[156] A1: dramc_BA[2] A2: ebi_CS0 A3: flexpwm1_B[0]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
F1	GPIO	nexus MDO[10][1]	A0: siul_GPIO[109] A1: _ A2: npc_wrapper_MDO[10] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
F2	GPIO	nexus MDO[11][1]	A0: siul_GPIO[108] A1: _ A2: npc_wrapper_MDO[11] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
F3	GPIO	nexus MDO[6][1]	A0: siul_GPIO[113] A1: _ A2: npc_wrapper_MDO[6] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
F4	GPIO	nexus MDO[4][1]	A0: siul_GPIO[115] A1: _ A2: npc_wrapper_MDO[4] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
F20	GPIO	dramc RAS	A0: siul_GPIO[151] A1: dramc_RAS A2: ebi_WE_BE_0 A3: flexpwm0_A[2]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
F21	GPIO	siul GPIO[194]	A0: siul_GPIO[194] A1: flexpwm0_X[0] A2: ebi_AD28 A3: _	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
F22	GPIO	siul GPIO[148]	A0: siul_GPIO[148] A1: _ A2: ebi_CLKOUT A3: flexpwm0_B[0]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
F23	GPIO	dramc D[5]	A0: siul_GPIO[179] A1: dramc_D[5] A2: ebi_AD13 A3: ebi_ADD29	I: _ I: _ I: _	—	disabled	DRAM DQ	VDD_HV_DRAM

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
G1	GPIO	nexus MCKO	A0: siul_GPIO[87] A1: _ A2: npc_wrapper_MCKO A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
G3	GPIO	nexus MDO[8][1]	A0: siul_GPIO[111] A1: _ A2: npc_wrapper_MDO[8] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
G4	GPIO	nexus MSEO_B[1][1]	A0: siul_GPIO[88] A1: _ A2: npc_wrapper_MSEO_B[1] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
G20	GPIO	siul GPIO[196]	A0: siul_GPIO[196] A1: flexpwm0_X[2] A2: ebi_AD30 A3: _	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
G21	GPIO	dramc DQS[0]	A0: siul_GPIO[190] A1: dramc_DQS[0] A2: ebi_AD24 A3: _	I: _ I: _ I: _	—	disabled	DRAM DQ	VDD_HV_DRAM
G22	GPIO	dramc DM[0]	A0: siul_GPIO[192] A1: dramc_DM[0] A2: ebi_AD26 A3: _	I: _ I: _ I: _	—	disabled	DRAM DQ	VDD_HV_DRAM
G23	GPIO	dramc D[7]	A0: siul_GPIO[181] A1: dramc_D[7] A2: ebi_AD15 A3: ebi_ADD31	I: _ I: _ I: _	—	disabled	DRAM DQ	VDD_HV_DRAM
H1	GPIO	nexus EVTO_B	A0: siul_GPIO[90] A1: _ A2: npc_wrapper_EVTO_B A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
H3	GPIO	nexus MSEO_B[0][1]	A0: siul_GPIO[89] A1: _ A2: npc_wrapper_MSEO_B[0] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
T2	GPIO	flexpwm1 A[0]	A0: siul_GPIO[117] A1: flexpwm1_A[0] A2: _ A3: can2_TXD	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
T3	GPIO	flexpwm1 A[1]	A0: siul_GPIO[120] A1: flexpwm1_A[1] A2: _ A3: can3_TXD	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
T20	GPIO	dramc ADD[8]	A0: siul_GPIO[166] A1: dramc_ADD[8] A2: ebi_AD0 A3: ebi_ADD16	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
T21	GPIO	dramc ADD[9]	A0: siul_GPIO[167] A1: dramc_ADD[9] A2: ebi_AD1 A3: ebi_ADD17	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
T22	GPIO	dramc ADD[1]	A0: siul_GPIO[159] A1: dramc_ADD[1] A2: ebi_ADD9 A3: ebi_CS3	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
U1	GPIO	flexpwm1 B[0]	A0: siul_GPIO[118] A1: flexpwm1_B[0] A2: _ A3: _	I: can2_RXD I: can3_RXD I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
U2	GPIO	flexpwm1 B[1]	A0: siul_GPIO[121] A1: flexpwm1_B[1] A2: _ A3: _	I: can3_RXD I: can2_RXD I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
U3	GPIO	flexpwm1 A[2]	A0: siul_GPIO[123] A1: flexpwm1_A[2] A2: _ A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
U4	GPIO	dspi2 SCK	A0: siul_GPIO[11] A1: dspi2_SCK A2: _ A3: _	I: can3_RXD I: _ I: siul_EIRQ[10]	—	disabled	GP Slow/ Medium	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
AC10	ANA	adc0 AN[1]	—	siul_GPI[24] etimer0_ETC[5]	AN: adc0_AN[1]	—	Analog	VDD_HV_ADR0
AC11	ANA	adc0 AN[3]	—	siul_GPI[34]	AN: adc0_AN[3]	—	Analog	VDD_HV_ADR0
AC14	ANA	adc0_adc1 AN[14]	—	siul_GPI[28]	AN: adc0_adc1_AN[14]	—	Analog Shared	VDD_HV_ADR0
END OF 473 MAPBGA PIN MULTIPLEXING TABLE								

[1] Do not connect pin directly to a power supply or ground.

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA} \quad \textit{Eqn. 2}$$

where:

$R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)

$R_{\theta JC}$ = junction to case thermal resistance (°C/W)

$R_{\theta CA}$ = case to ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To determine the junction temperature of the device in the application when heat sinks are not used, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using Equation 3:

$$\mathbf{T_J = T_T + (\Psi_{JT} \times P_D)} \quad \textit{Eqn. 3}$$

where:

T_T = thermocouple temperature on top of the package (°C)

Ψ_{JT} = thermal characterization parameter (°C/W)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

See [6] to [10] in Section 6, Reference documents, for more information.

3.5 Electromagnetic interference (EMI) characteristics

3.5.1 Test Setup

Electromagnetic emission tests are performed by TEM cell [2] and via direct coupling [3] (150 Ω) measurements.

Electromagnetic immunity is measured by DPI [4].

See Section 6, Reference documents, for more information.

3.5.2 Test parameters

The following test parameters shall be used:

Table 14. EMC test parameters

Method	Frequency Range	Receiver	
		BW	Step Size
150 Ω	1 MHz to 1000 MHz	1 MHz	500 kHz
TEM			

3.17.2 GP pads AC specifications

Table 34. GP pads AC electrical characteristics[1]

No.	Pad	Tswitchon[1] (ns)			Rise/Fall[2] (ns)			Frequency (MHz)			Current slew[3] (mA/ns)			Load drive (pF)
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
1	Slow	3	—	40	4	—	40	—	—	4	0.01	—	2	25
		3	—	40	6	—	50	—	—	2	0.01	—	2	50
		3	—	40	10	—	75	—	—	2	0.01	—	2	100
		3	—	40	14	—	100	—	—	2	0.01	—	2	200
2	Medium	1	—	15	2	—	12	—	—	40	2.5	—	7	25
		1	—	15	4	—	25	—	—	20	2.5	—	7	50
		1	—	15	8	—	40	—	—	13	2.5	—	7	100
		1	—	15	14	—	70	—	—	7	2.5	—	7	200
3	Fast	1	—	6	1	—	4	—	—	72	3	—	40	25
		1	—	6	1.5	—	7	—	—	55	7	—	40	50
		1	—	6	3	—	12	—	—	40	7	—	40	100
		1	—	6	5	—	18	—	—	25	7	—	40	200
4	Symmetric	1	—	8	1	—	5	—	—	50	3	—	25	25
5	Pullup/down (3.6 V max)	—	—	—	—	—	7500	—	—	—	—	—	—	50

1 The values provided in this table are not applicable for PDI and EBI/DRAM interface.

2 Slope at rising/falling edge.

3 Data based on characterization results, not tested in production.

3.18 PDI pads specifications

This section specifies the electrical characteristics of the PDI pads. Please refer to the tables in Section 2.2, Pin descriptions, for a cross reference between package pins and pad types.

PDI pads feature list:

- Direction
  - Input
  - Output
  - Bidirectional
- Driver
  - Push/Pull/Open Drain
  - Configurable Four Drive Strengths on Fast driver pads
  - Configurable No Slew-Rate, Slow Slew-Rate, and Fast Slew-Rate on Slow, Medium, and SLR driver pads
  - VDD_HV_PDI NOTE: All pads are NOT 5 V TOLERANT. Pads are not capable of driving to or from voltages above their respective VDD_HV_PDI. In other words, you cannot connect a 3.3V external device to a pad

– 150 Ω

The electrical data provided in Section 3.19, DRAM pad specifications, applies to the pads listed in Table 39.

Table 39. DRAM pads

Name	Voltage	Used For	Notes[1]
DRAM ACC	1.62 V–3.6 V	I/O	Bidirectional DDR pad
DRAM CLK	1.62 V–3.6 V	O	Output only differential clock driver pad
DRAM DQ	1.62 V–3.6 V	I/O	Bidirectional DDR pad with integrated ODT

1 All pads can be configured to support LPDDR half strength, LPDDR full strength, DDR1, DDR2 half strength, DDR2 full strength, and SDR.

All three pad types can be configured to support SDR, DDR, DDR2 half and full strength, and LPDDR half and full strength modes, according to Table 40.

Table 40. Mode configuration for DRAM pads

Configuration[1]	Mode
000	1.8 V LPDDR Half Strength
001	1.8 V LPDDR Full Strength
010	1.8 V DDR2 Half Strength
011	2.5 V DDR
100	Not supported
101	Not supported
110	1.8 V DDR2 Full Strength
111	SDR

1 Configuration is selected in the corresponding PCR registers of the SIUL.

NOTE

0.7 V overshoot/undershoot can be allowed to occur repeatedly throughout the product expected lifetime and will not cause any long term reliability issue.

3.19.1 DRAM pads electrical specifications ($V_{DD\_HV\_DRAM}$ = 3.3 V)

Table 41. DRAM pads DC electrical specifications ($V_{DD\_HV\_DRAM}$ = 3.3 V)

No.	Symbol		Parameter	Condition	Min	Max	Unit
1	$V_{DD\_HV\_DRAM}$	SR	I/O supply voltage	—	3.0	3.6	V
2	$V_{DD\_HV\_DRAM\_VREF}$	CC	Input reference voltage	—	1.3	1.7	V
3	$V_{DD\_HV\_DRAM\_VTT}$	CC	Termination voltage[1]	—	$V_{DD\_HV\_DRAM\_VREF}$ − 0.05	$V_{DD\_HV\_DRAM\_VREF}$ + 0.05	V
4	V_{IH}	CC	Input high voltage	—	$V_{DD\_HV\_DRAM\_VREF}$ + 0.20	—	V

3.21.4.3 External reset via $\overline{\text{RESET}}$

Figure 20 shows the voltage thresholds that determine the start of the reset sequences initiated by the assertion of $\overline{\text{RESET}}$ as specified in Table 53.

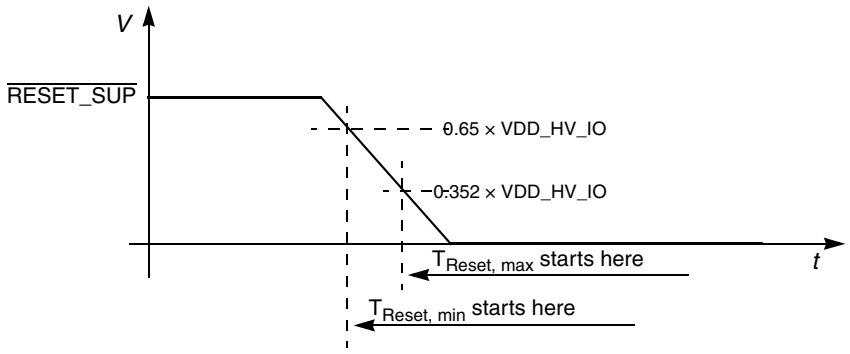

Figure 20. Reset sequence start via $\overline{\text{RESET}}$ assertion

3.21.5 External watchdog window

If the application design requires the use of an external watchdog the data provided in Section 3.21, Reset sequence can be used to determine the correct positioning of the trigger window for the external watchdog. Figure 21 shows the relationships between the minimum and the maximum duration of a given reset sequence and the position of an external watchdog trigger window.

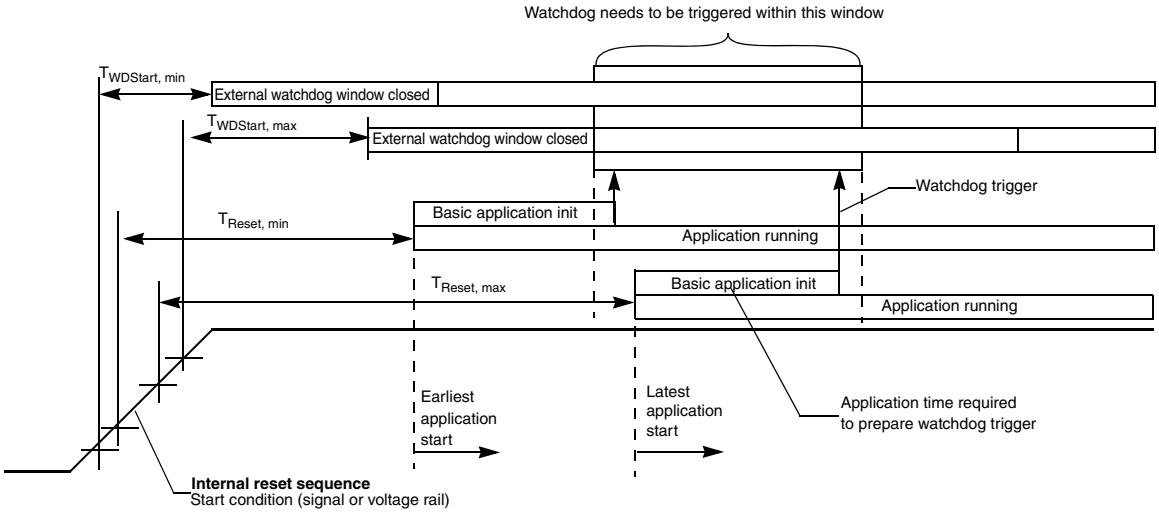

Figure 21. Reset sequence—external watchdog trigger window position

3.22 Peripheral timing characteristics

3.22.1 SDRAM (DDR)

The MPC5675K memory controller supports three types of DDR devices:

- DDR-1 (SSTL_2 class II interface)
- DDR-2 (SSTL_18 interface)
- LPDDR/Mobile-DDR (1.8V I/O supply voltage)

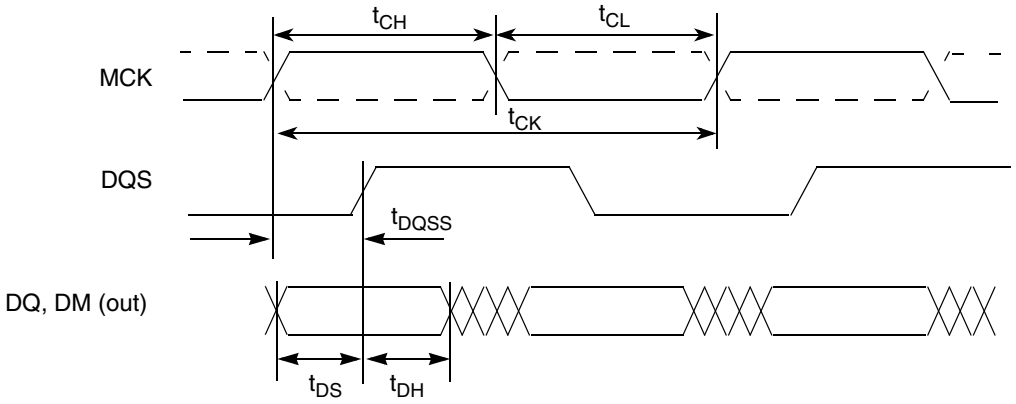

Figure 22. DDR write timing

Figure 23 and Figure 24 show the DDR SDRAM read timing.

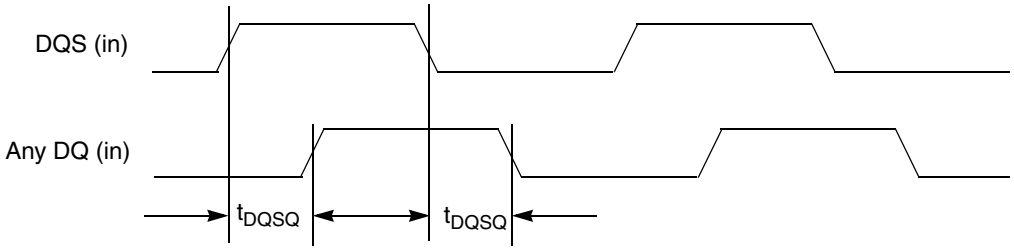

Figure 23. DDR read timing, DQ vs. DQS

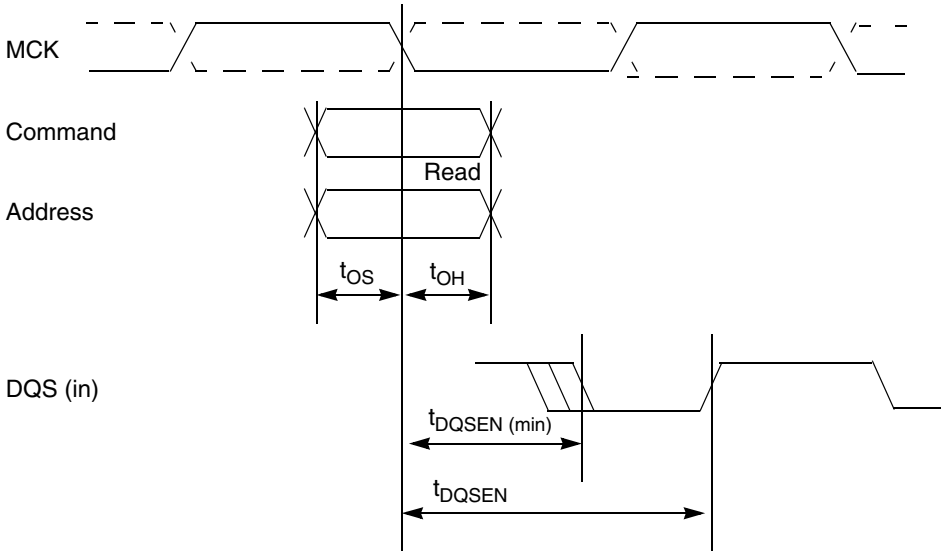

Figure 24. DDR read timing, DQSEN

Figure 25 provides the AC test load for the DDR bus.

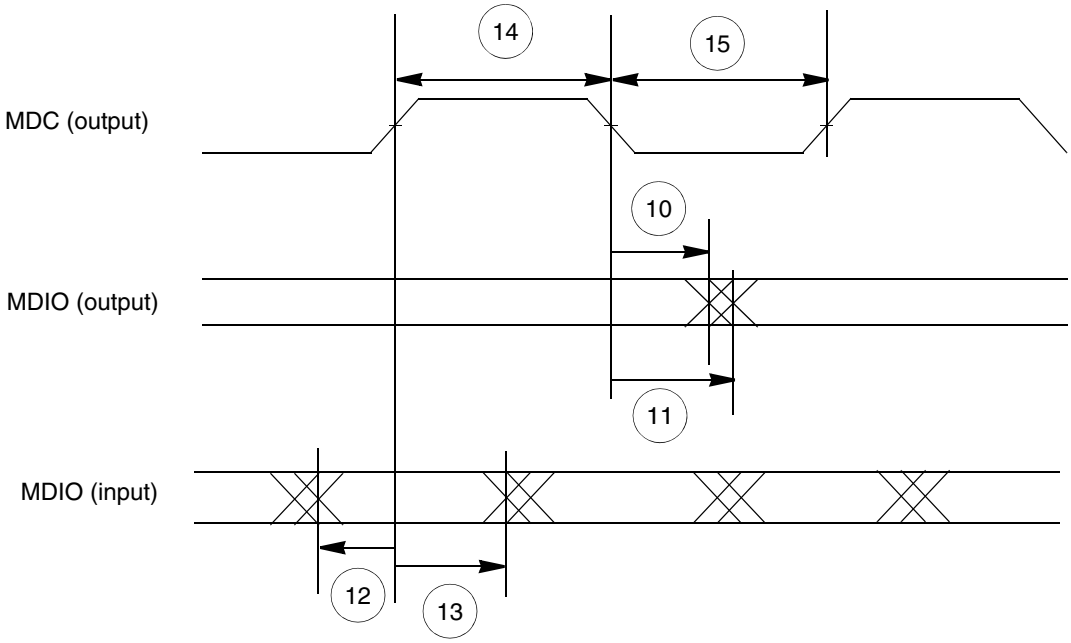

Figure 48. MII serial management channel timing diagram

3.22.9 External Bus Interface (EBI) timing

Table 70. EBI timing

No.	Symbol		Parameter	45 MHz (Ext. Bus Freq)[1]		Unit	Notes
				Min	Max		
1	t_C	CC	D_CLKOUT period	22.2	—	ns	Signals are measured at 50% V_{DDE}.
2	t_{CDC}	CC	D_CLKOUT duty cycle	45%	55%	t_C	—
3	t_{CRT}	CC	D_CLKOUT rise time	—	—	ns	—
4	t_{CFT}	CC	D_CLKOUT fall time	—	—	ns	—
5	t_{COH}	CC	D_CLKOUT posedge to output signal invalid or high Z (hold time) D_ADD[9:30] D_BDIP D_CS[0:3] D_DAT[0:15] D_OE $\overline{\text{D\_RD\_WR}}$ D_TA D_TS $\overline{\text{D\_WE}}$[0:3]/$\overline{\text{D\_BE}}$[0:3]	1.0	—	ns	—

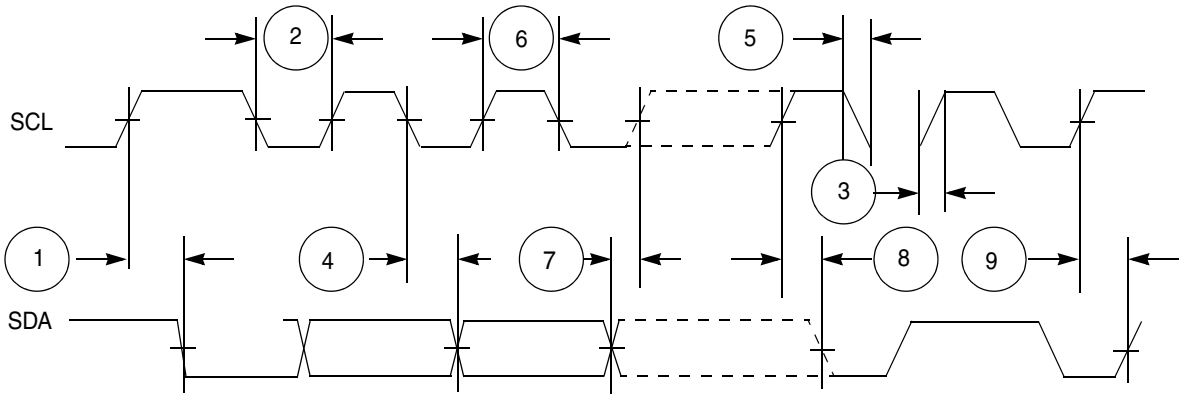

Figure 53. I²C input/output timing

3.22.11 LINFlex timing

The maximum bit rate is 1.875 MBit/s.